PNP/NPN Epitaxial Planar Silicon Transistors



2SB1135/2SD1668

50V/7A Switching Applications

Applications

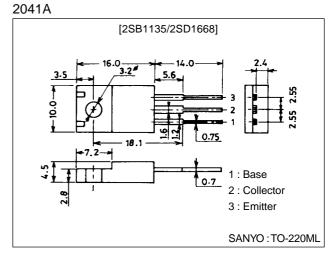
• Relay drivers, high-speed inverters, converters, and other general high-current switching applications.

Features

- \cdot Low-saturation collector-to-emitter voltage :
- V_{CE(sat)}=-0.4V max.
- \cdot Wide ASO leading to high resistance to breakdown.
- · Micaless package facilitating mounting.

Package Dimensions

unit:mm



():2SB1135

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		(–)60	V
Collector-to-Emitter Voltage	VCEO		(–)50	V
Emitter-to-Base Voltage	VEBO		()6	V
Collector Current	ι _C		(-)7	А
Collector Current (Pulse)	ICP		(–)12	A
Collector Dissipation	PC		2	W
		Tc=25°C	30	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =(-)40V, I _E =0			(–)0.1	mA
Emitter Cutoff Current	IEBO	V _{EB} =(-)4V, I _C =0			(–)0.1	mA
DC Current Gain	h _{FE} 1	V _{CE} =(-)2V, I _C =(-)1A	70*		280*	
	h _{FE} 2	V _{CE} =(-)2V, I _C =(-)5A	30			
Gain-Bandwidth Product	fT	V _{CE} =(-)5V, I _C =(-)1A		10		MHz
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =(-)4A, I _B =(-)0.4A			(-)0.4	V

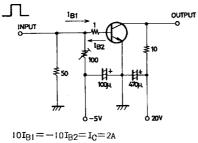
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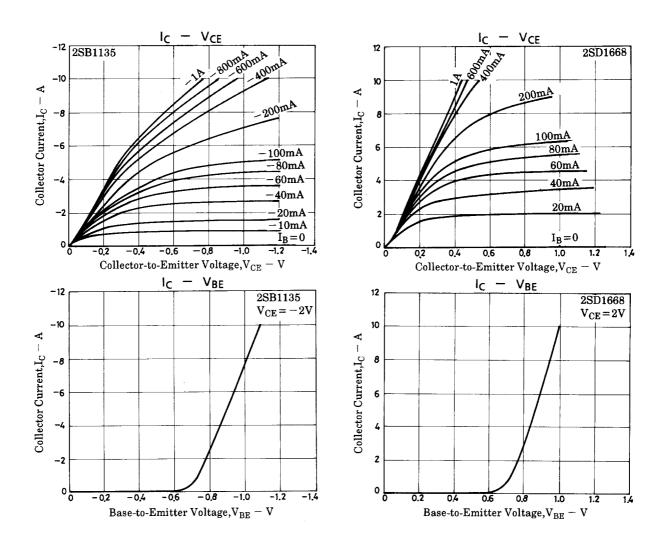
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Parameter	Symbol	Conditions		Ratings		
			min	typ	max	Unit
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =(-)1mA, I _E =0	(–)60			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =(−)1mA, R _{BE} =∞	(–)50			V
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	I _E =(-)1mA, I _C =0	(–)6			V
Rise Time	ton	See specified Test Circuti.		0.2		μs
Storage Time	^t stg	See specified Test Circuit.		(0.7)		μs
				0.9		μs
Fall Time	tf	See specified Test Circuit.		(0.1)		μs
				0.3		μs

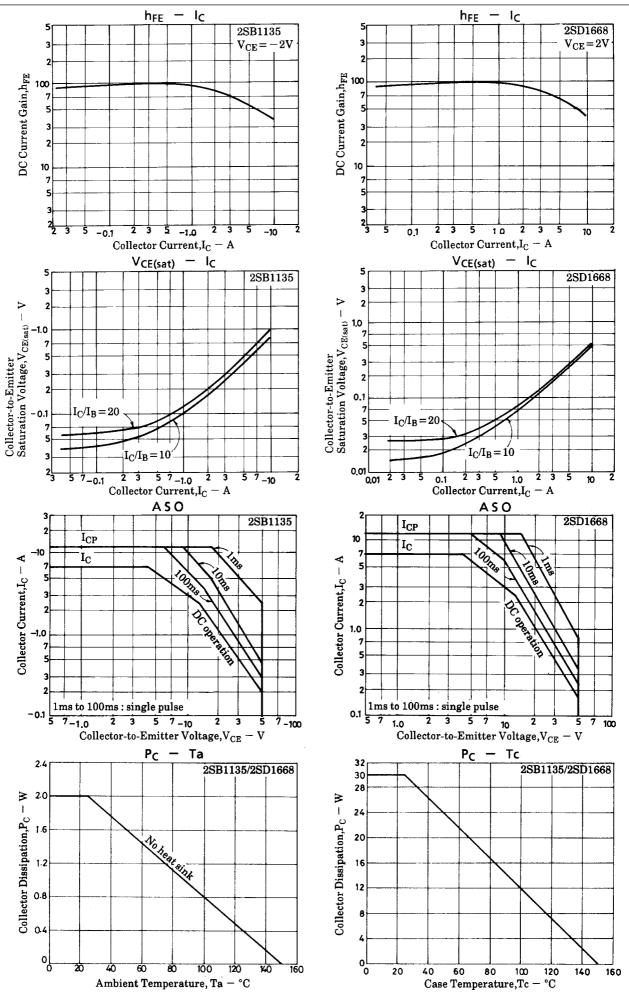
Switching Time Test Circuit



For PNP, the polarity is reversed. Unit (resistance : Ω , capacitance : F)



2SB1135/2SD1668



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